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(71)Applicant : SEMICONDUCTOR ENERGY LAB CO LTD

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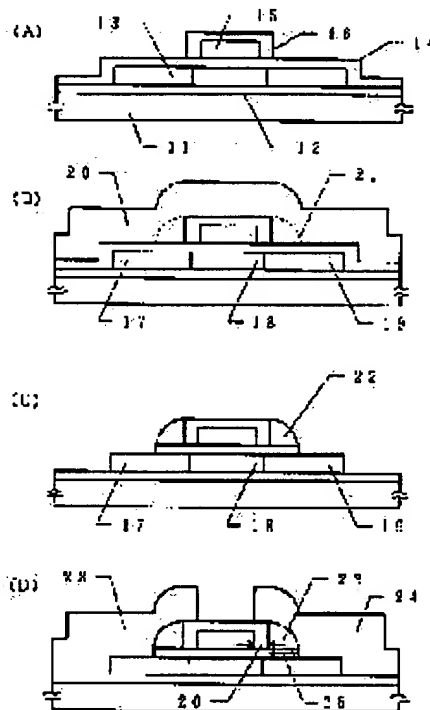
(72)Inventor : TERAMOTO SATOSHI
CHIYOU KOUYUU
TAKEMURA YASUHIKO

(54) SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

(57)Abstract:

PURPOSE: To accurately form a contact hole in source/drain regions in a location close to a channel forming region by a method wherein substantially triangular insulated matter closely connected to an insulation layer in a gate electrode side surface is provided, whereby a contact location for the source/drain regions is specified.

CONSTITUTION: Substantially triangular insulated matter 22 closely connected to an insulation layer 16 in a gate electrode 15 side surface is provided, whereby a contact location for the source/drain regions 17, 19 is specified. For example, an Al film formed by a sputter method is patterned to form the gate electrode 15 and the surface is anode-oxidized to form the oxide layer 16. Next, impurities are doped onto a crystalline silicon film 13 by an ion implantation method and the source/drain regions 17, 19 are self-adjustably formed to form a silicon oxide film 20 by a sputter method. Next, anisotropic dry-etching is performed to leave the silicon oxide 22 formed in substantially a triangular form.



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